

DSA7506

Silicon PNP epitaxial planar type

For low frequency amplification

■ Features

- Low collector-emitter saturation voltage $V_{CE(sat)}$
- Halogen-free / RoHS compliant
(EU RoHS / UL-94 V-0 / MSL: Level 1 compliant)

■ Marking Symbol: 4LR

■ Packaging

DSA7506R0L Embossed type (Thermo-compression sealing): 1 000 pcs / reel (standard)

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	-30	V
Collector-emitter voltage (Base open)	V_{CEO}	-25	V
Emitter-base voltage (Collector open)	V_{EBO}	-11	V
Collector current	I_C	-3	A
Peak collector current *1	I_{CP}	-10	A
Collector power dissipation *2	P_C	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Operating ambient temperature	T_{opr}	-40 to +85	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *1: Pulse width $\leq 1\text{ms}$, Single pulse

*2: Printed circuit board: Copper foil area of 1 cm^2 or more, and the board thickness of 1.7 mm for the collector portion

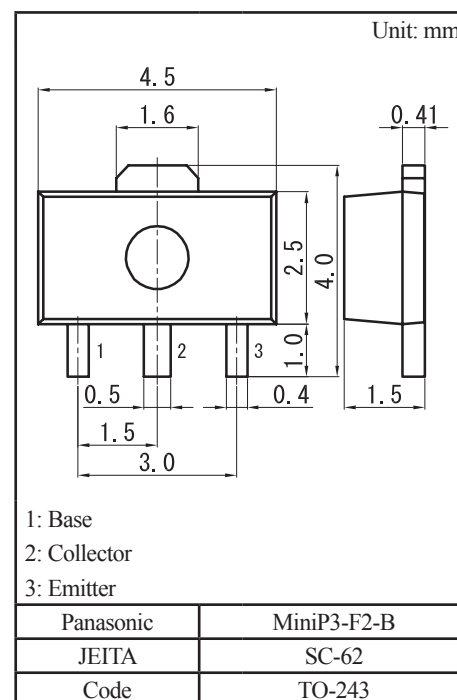
■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

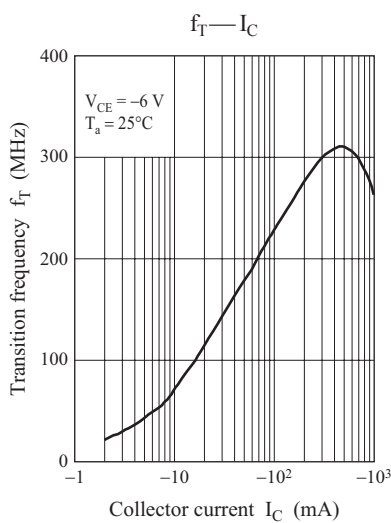
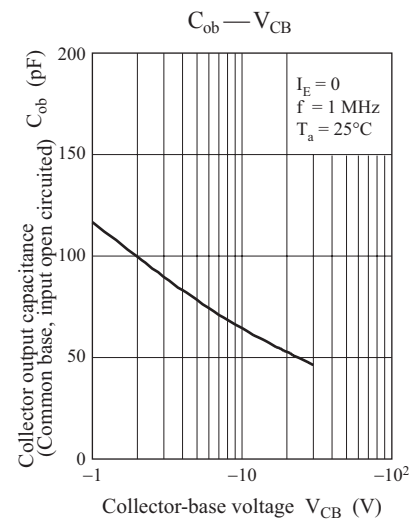
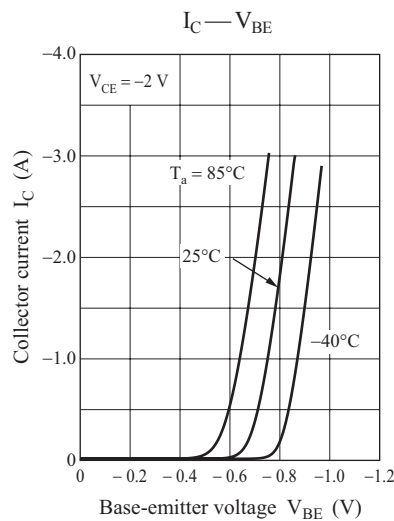
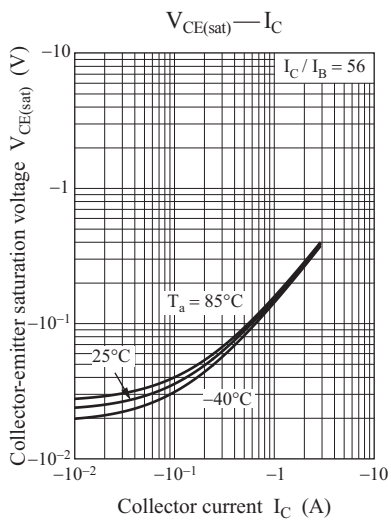
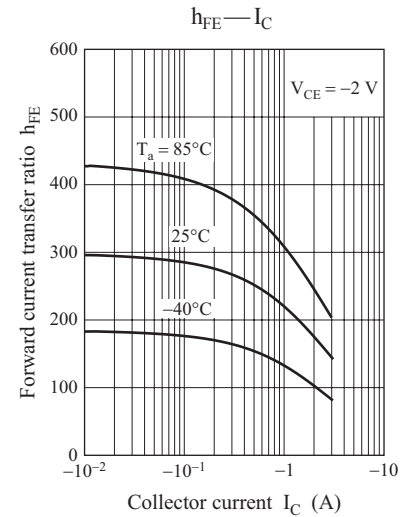
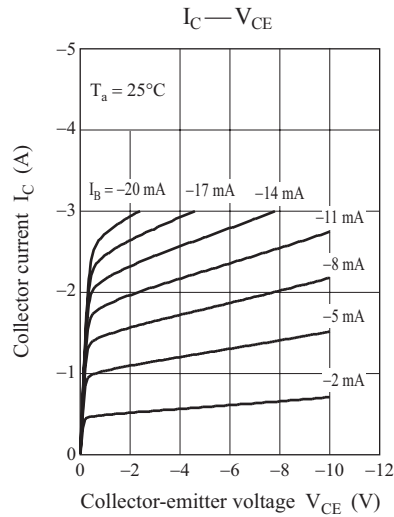
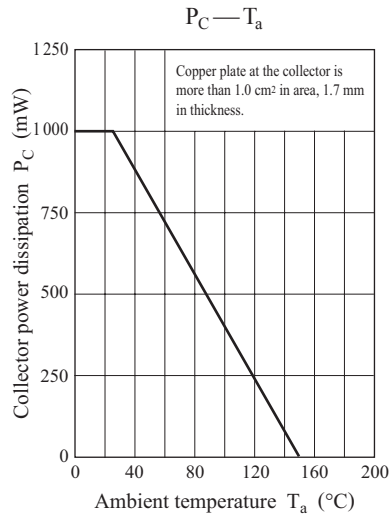
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)	V_{CBO}	$I_C = -10\text{ }\mu\text{A}$, $I_E = 0$	-30			V
Collector-emitter voltage (Base open)	V_{CEO}	$I_C = -1\text{ mA}$, $I_B = 0$	-25			V
Emitter-base voltage (Collector open)	V_{EBO}	$I_E = -10\text{ }\mu\text{A}$, $I_C = 0$	-11			V
Forward current transfer ratio *1, 2	h_{FE}	$V_{CE} = -2\text{ V}$, $I_C = -1.4\text{ A}$	130		450	—
Collector-emitter saturation voltage *1	$V_{CE(sat)}$	$I_C = -1.4\text{ A}$, $I_B = -25\text{ mA}$		-0.2	-0.27	V
Transition frequency	f_T	$V_{CE} = -6\text{ V}$, $I_C = -50\text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C_{ob}	$V_{CB} = -10\text{ V}$, $I_E = 0$, $f = 1\text{ MHz}$			85	pF

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *1: Pulse measurement

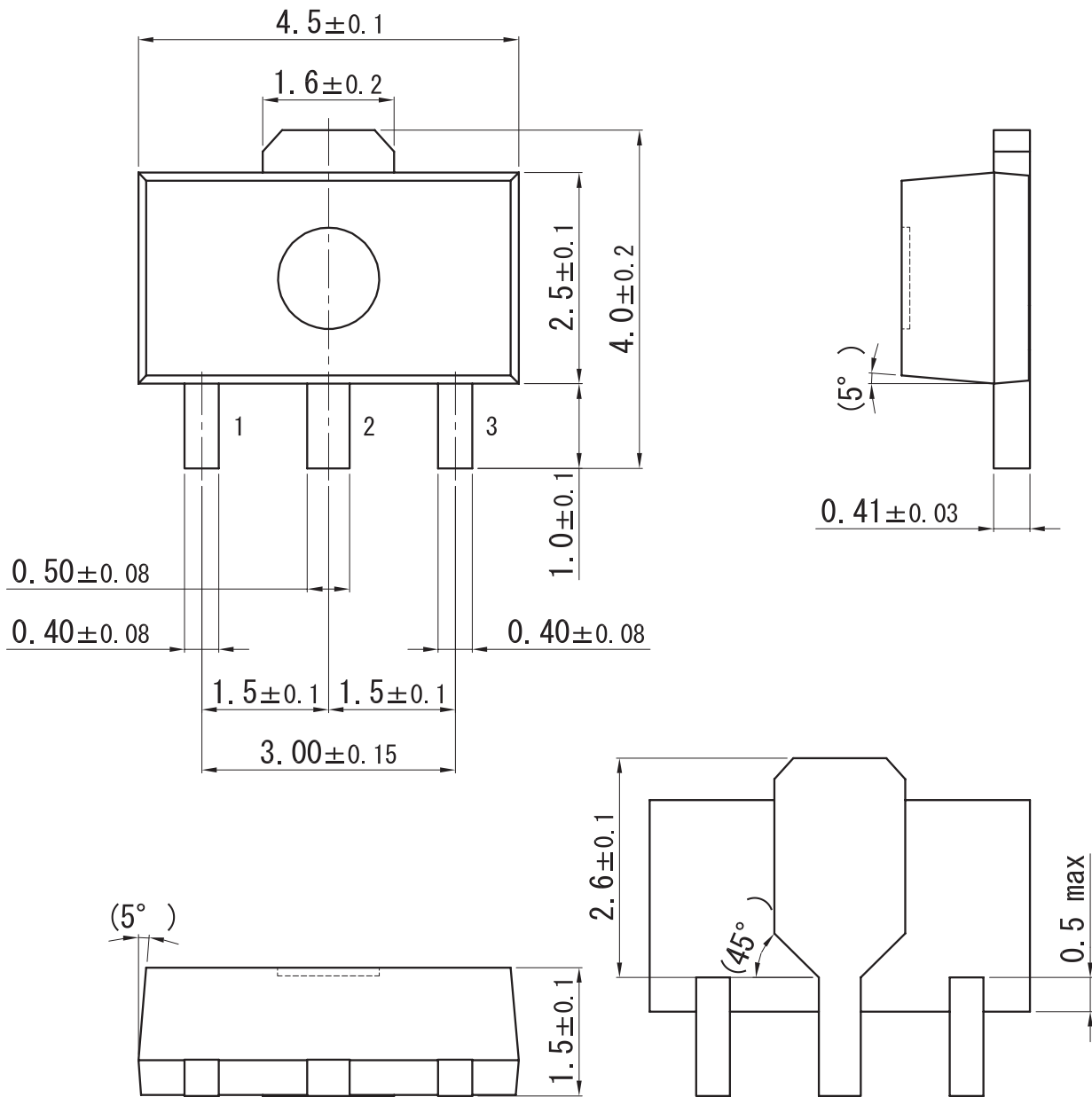
*2: Rank classification: Only R rank producing.



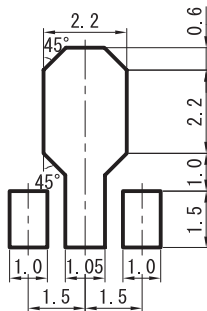


MiniP3-F2-B

Unit: mm



■ Land Pattern (Reference) (Unit: mm)



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